ABSTRACT

The present technology relates to an electronic device. According to the present technology, a memory device having improved verify accuracy may include a memory block including memory cells, a read and write circuit including a plurality of page buffers, a current sensing circuit configured to perform a verify operation of comparing sensing voltages with a reference voltage, and a control logic configured to control the current sensing circuit to perform the verify operation. The control logic controls performing a first verify operation on each of page buffer groups having a same logical group number, and performing a second verify operation on each of page buffer groups having a same physical group number, and the current sensing circuit outputs a verify pass signal in response to both results of the first verify operation and the second verify operation satisfying a pass criterion.

FIG. 1